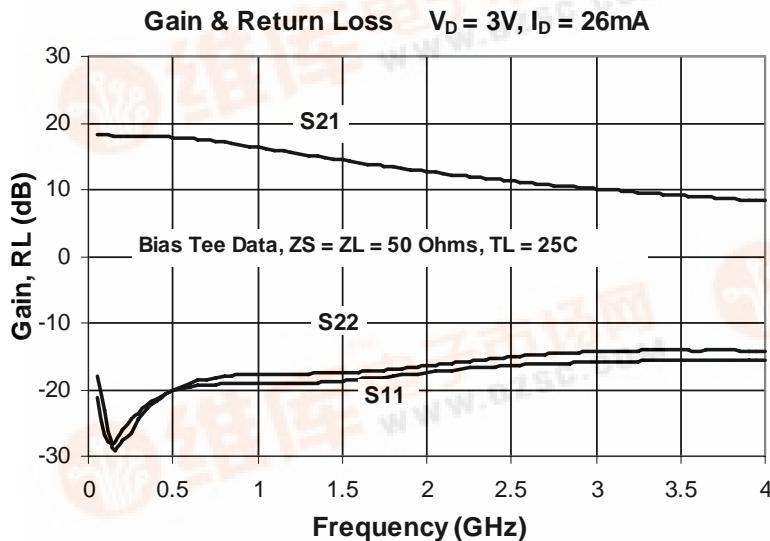




Product Description

Sirenza Microdevices' SGC-2386Z is a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with a patented active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 3V supply, the SGC-2386Z does not require a dropping resistor as compared to typical Darlington amplifiers. The SGC-2386Z is designed for high linearity 3V gain block applications that require small size and minimal external components. It is internally matched to 50 ohms.



SGC-2386Z

50-4000 MHz Active Bias Silicon Germanium Cascadable Gain Block



RoHS Compliant & Green Package

Product Features

- Single Fixed 3V Supply
- No Dropping Resistor Required
- Patented Self-Bias Circuitry
- $P_{1dB} = 9.7$ dBm at 1950 MHz
- $OIP_3 = 23$ dBm at 1950 MHz
- Robust 1000V ESD, Class 1C HBM

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS, WCDMA
- IF Amplifier
- Wireless Data, Satellite

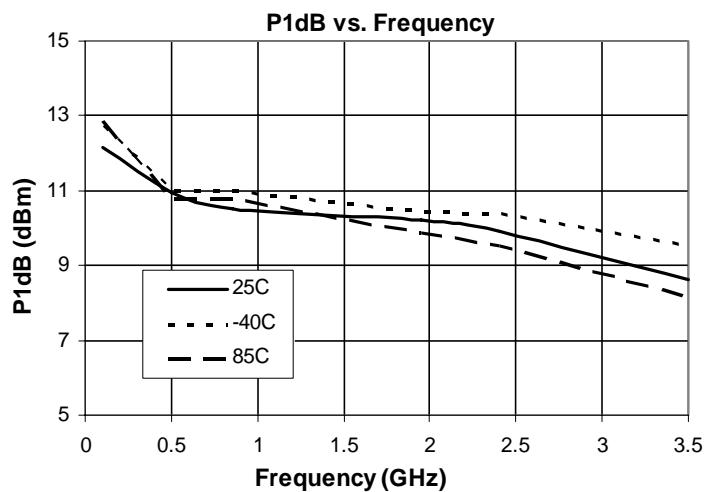
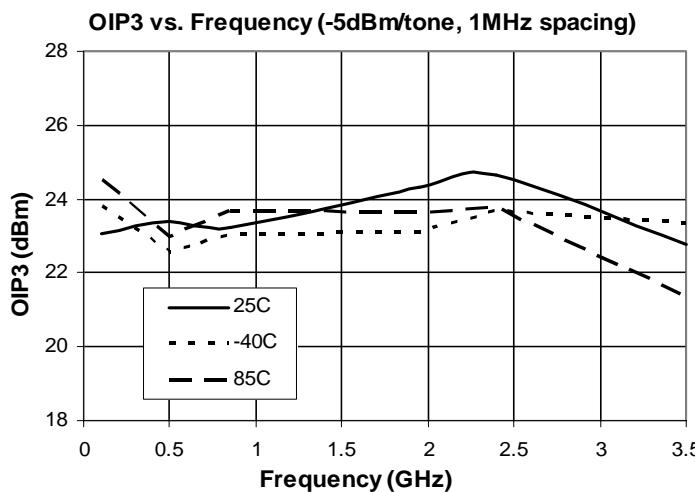
Symbol	Parameters	Units	Frequency	Min.	Typ.	Max.
G	Small Signal Gain	dB	850 MHz 1950 MHz 2400 MHz	15.5 11 11.4	17.0 12.5 11.4	18.5 14
P_{1dB}	Output Power at 1dB Compression	dBm	850 MHz 1950 MHz 2400 MHz	8.7	10.5 9.7 9.9	
OIP_3	Output Third Order Intercept Point	dBm	850 MHz 1950 MHz 2400 MHz	21	23.0 23.0 24.5	
IRL	Input Return Loss	dB	1950 MHz	14.0	18.0	
ORL	Output Return Loss	dB	1950 MHz	12.5	16.5	
NF	Noise Figure	dB	1930 MHz		3.8	4.8
V_D	Device Operating Voltage	V			3	
I_D	Device Operating Current	mA		22	26	30
$R_{th, j-l}$	Thermal Resistance (junction to lead)	$^{\circ}C/W$			205	
Test Conditions: $V_D = 3.0V$ $I_D = 26mA$ $T_L = 25^{\circ}C$			OIP_3 Tone Spacing = 1MHz			
Bias Tee Data			$Z_S = Z_L = 50$ Ohms			
			Pout per tone = -5 dBm			

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Typical RF Performance at Key Operating Frequencies (Bias Tee)						
Symbol	Parameter	Unit	Frequency (MHz)			
			100	500	850	1950
G	Small Signal Gain	dB	18.4	18.0	17.0	12.5
OIP ₃	Output Third Order Intercept Point	dBm	23.5	23.5	23.0	24.5
P _{1dB}	Output Power at 1dB Compression	dBm	11.0	11.0	10.5	10.2
IRL	Input Return Loss	dB	24.0	19.0	20.0	18.0
ORL	Output Return Loss	dB	23.0	18.5	19.0	16.5
S ₁₂	Reverse Isolation	dB	20.5	21.5	22.0	20.0
NF	Noise Figure	dB	2.9	3.0	3.3	3.8

Test Conditions: V_D = 3V I_D = 26mA Typ. OIP₃ Tone Spacing = 1MHz, Pout per tone = -5 dBm
T_L = 25°C Z_S = Z_L = 50 Ohms

Typical Performance with Bias Tee, V_D = 3V, I_D = 26mA



Absolute Maximum Ratings		Reliability & Qualification Information	
Parameter	Absolute Limit	Parameter	Rating
Max Device Current (I _{CE})	55 mA	ESD Rating - Human Body Model (HBM)	Class 1C
Max Device Voltage (V _{CE})	4.5 V	Moisture Sensitivity Level	MSL 1
Max. RF Input Power* (See Note)	+18 dBm	This product qualification report can be downloaded at www.sirenza.com	
Max. Junction Temp. (T _J)	+150°C		
Operating Temp. Range (T _L)	-40°C to +85°C		
Max. Storage Temp.	+150°C		

*Note: Load condition, Z_L = 50 Ohms

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

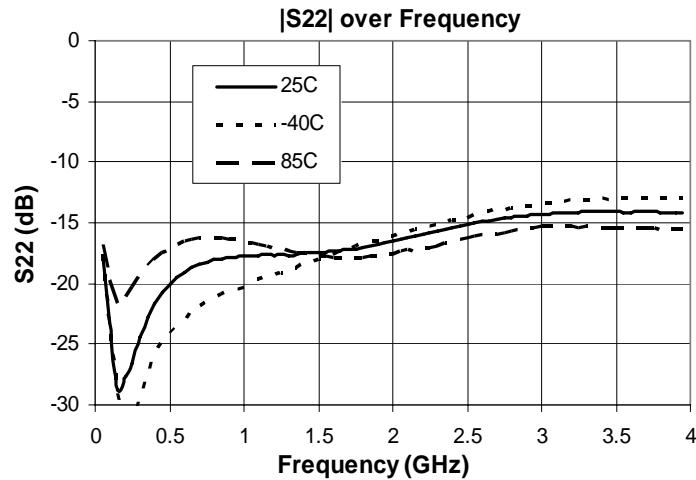
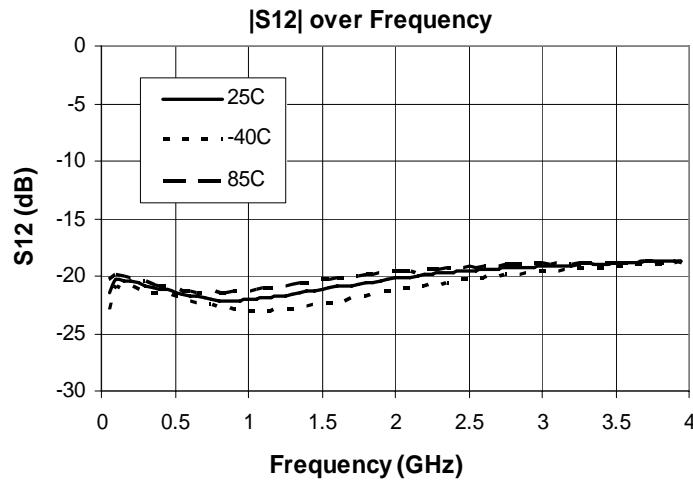
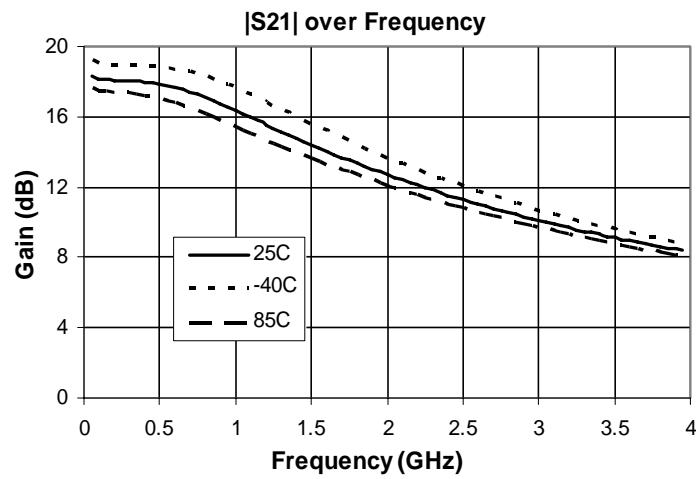
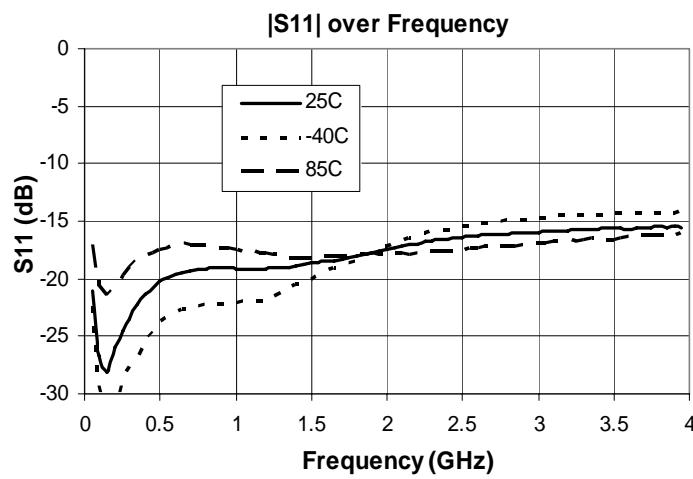
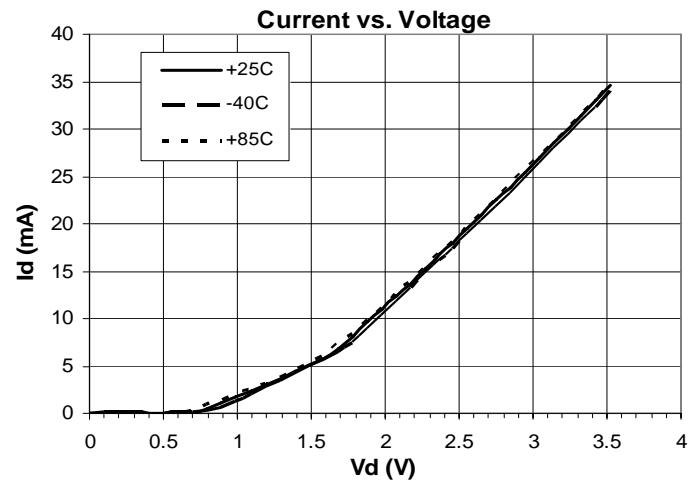
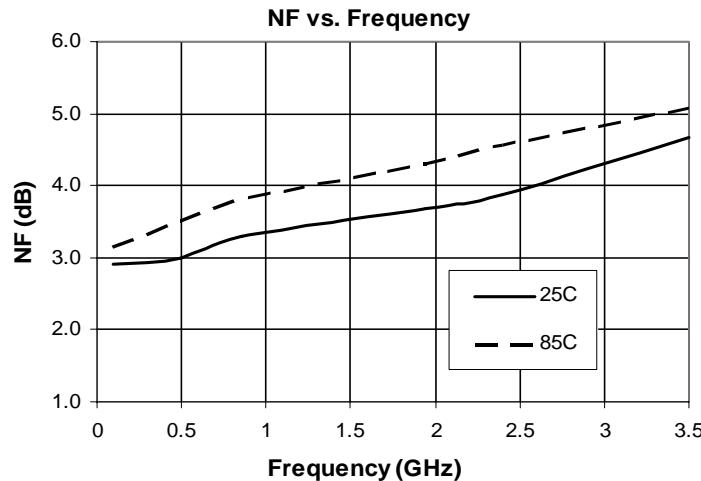
Bias Conditions should also satisfy the following expression:

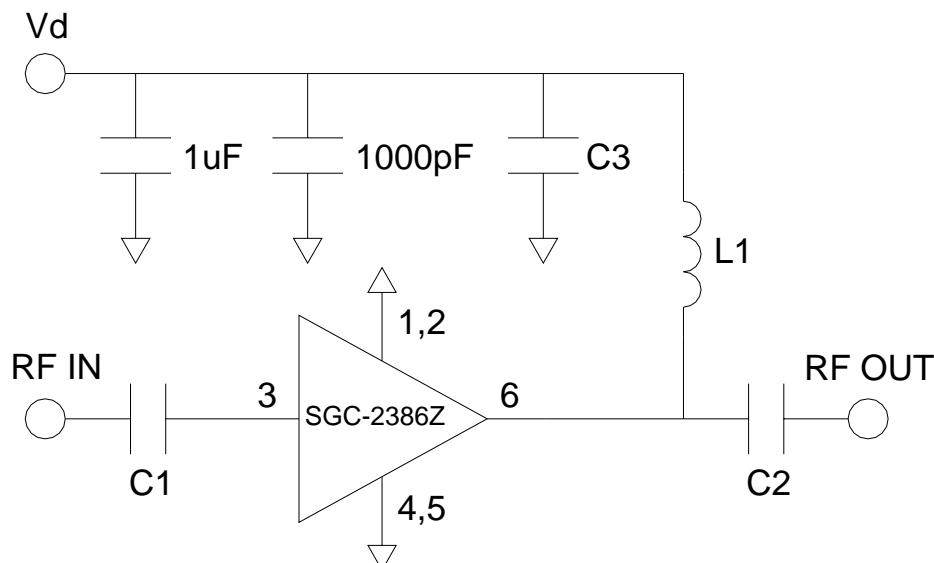
$$I_D V_D < (T_J - T_L) / R_{TH} \quad j-l \quad T_L = T_{LEAD}$$


Caution: ESD sensitive

Appropriate precautions in handling, packaging and testing devices must be observed.

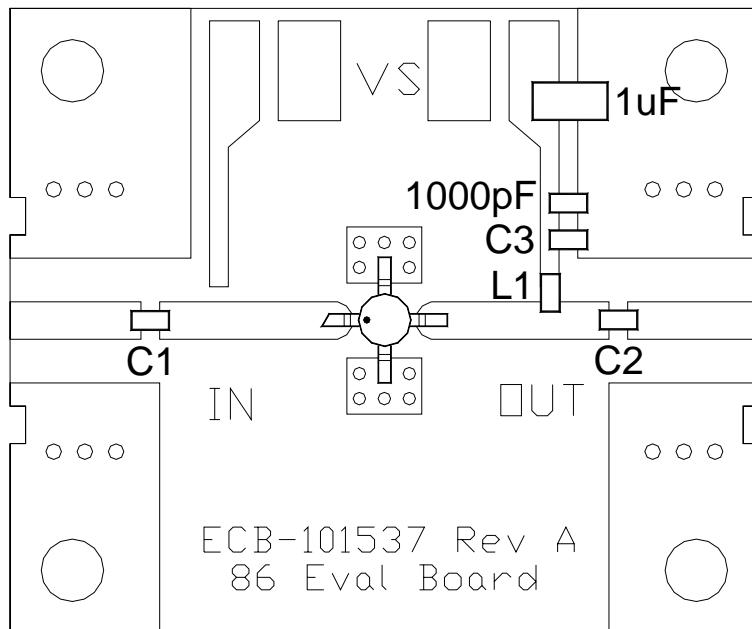
Typical Performance with Bias Tee, $V_D = 3V$, $I_D = 26mA$



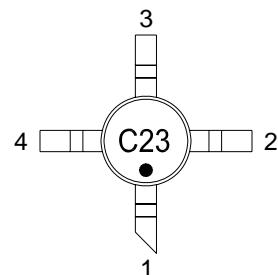


Application Circuit Schematic

Application Circuit Element Values		
Reference Designator	100-2000MHz	2000-4000MHz
C1	1000pF	2.7pF
C2	100pF	6.8pF
C3	100pF	6.8pF
L1	150nH	39nH



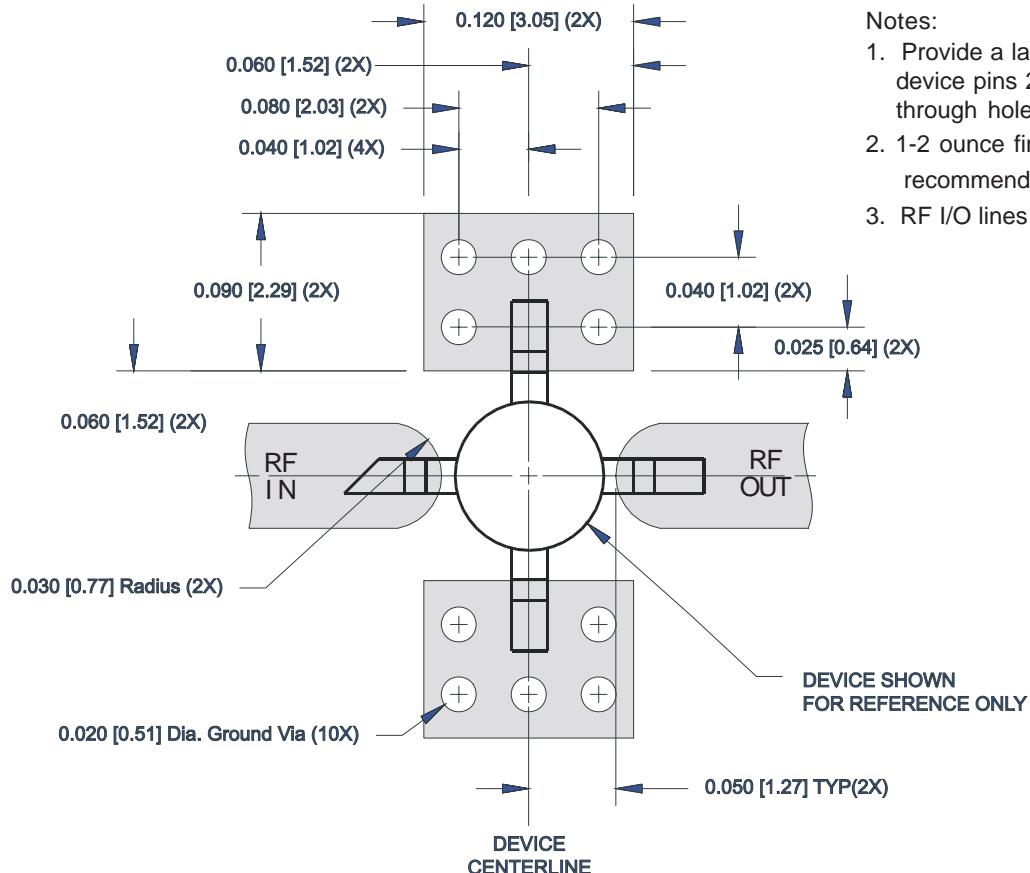
Part Identification Marking & Pinout



Pin #			Description				
			Part / Evaluation Board Ordering Information				
Pin #	Function	Description	Part Number		Description	Reel Size	Devices / Reel
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation	SGC-2386Z		Lead Free, RoHs Compliant	13"	3000
2,4	GND	Connection to ground. Use via holes as close to the device ground leads as possible to reduce ground inductance and achieve optimum RF performance	SGC-2386Z-EVB1		100-2000 MHz Evaluation Board	N/A	N/A
			SGC-2386Z-EVB2		2000-4000 MHz Evaluation Board	N/A	N/A
3	RF OUT / DC BIAS	RF output and bias pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.					

86 PCB Pad Layout

Dimensions in inches [millimeters]



86 Nominal Package Dimensions

Dimensions in inches [millimeters]

A link to the 86 package outline drawing with full dimensions and tolerances may be found on the product web page at www.sirenza.com.

